

SS8550 PNP Silicon General Purpose Transistor

RoHS Compliant Product A suffix of "-C" specifies halogen & lead-free

FEATURES

Power dissipation

P_{CM}: 0.3 W

Collector Current

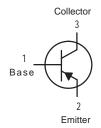
I_{CM}: - 1.5 A

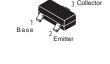
Collector-base voltage

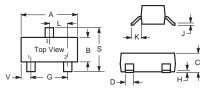
 $V_{(BR)CBO}$: - 40 V

• Operating & storage junction temperature

 T_J , T_{STG} : - 55°C ~ + 150°C







SOT-23						
Dim	Min	Max				
Α	2.800	3.040				
В	1.200	1.400				
С	0.890	1.110				
D	0.370	0.500				
G	1.780	2.040				
Н	0.013	0.100				
J	0.085	0.177				
K	0.450	0.600				
L	0.890	1.020				
S	2.100	2.500				
٧	0.450	0.600				
All Dimension in mm						

ELECTRICAL CHARACTERISTICS at Ta = 25°C

Symbol	Min.	Тур.	Max.	Unit	Test Conditions
BV _{CBO}	-40	-	-	V	$Ic = 100 \mu A, I_E = 0$
BV _{CEO}	-25	-	-	V	$Ic = -0.1 \text{mA}, I_B = 0$
BV _{EBO}	-5	-	-	V	$I_E = -100 \mu$ A, $I_C = 0$
I _{CBO}	-	-	-0.1	μΑ	$V_{CB} = -40 \text{ V}, I_{E} = 0$
I _{CEO}	-	-	-0.1	μА	V _{CE} = -20V, I _B = 0
I _{EBO}	-	-	-0.1	μА	$V_{EB} = -5V, I_{C} = 0$
V _{CE(sat)}	-	-	0.5	V	I _C = -800 mA, I _B = -80mA
V _{BE(sat)1}	-	-	1.2	V	I _C = -800 mA, I _B = -80mA
*h _{FE1}	120	-	350	-	V _{CE} = -1V, I _C =-100mA
*h _{FE2}	40	-	-	-	V _{CE} = -1V, I _C = -800mA
f _T	100	-	-	MHz	V _{CE} = -10V, I _C = -50mA, f = 30MHz
Сов	-	-	20	pF	V _{CB} = -10V, I _E =0, f=1MHz

CLASSIFICATION OF h_{FE(1)}

Rank	L	Н	J		
Range	120 - 200	200-350	300-400		
Marking	Y2				

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CHARACTERISTIC CURVES

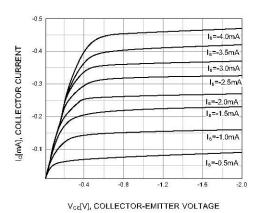


Figure 1. Static Characteristic

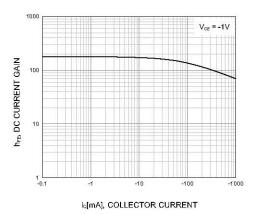


Figure 2. DC current Gain

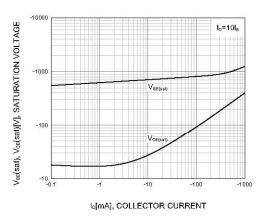


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

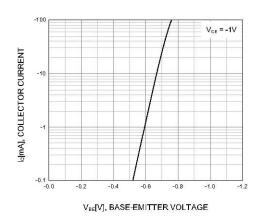


Figure 4. Base-Emitter On Voltage

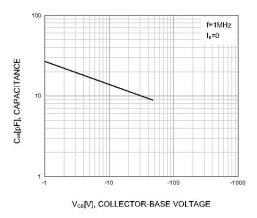


Figure 5. Collector Output Capacitance

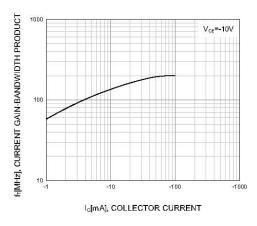


Figure 6. Current Gain Bandwidth Product

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